

Title (en)  
OPTOELECTRONIC SEMICONDUCTOR CHIP AND METHOD FOR ADAPTING A CONTACT STRUCTURE FOR ELECTRICALLY CONTACTING AN OPTOELECTRONIC SEMICONDUCTOR CHIP

Title (de)  
OPTOELEKTRONISCHER HALBLEITERCHIP UND VERFAHREN ZUM ANPASSEN EINER KONTAKTSTRUKTUR ZUR ELEKTRISCHEN KONTAKTIERUNG EINES OPTOELEKTRONISCHEN HALBLEITERCHIPS

Title (fr)  
PUCE À SEMI-CONDUCTEUR OPTOÉLECTRONIQUE ET PROCÉDÉ D'ADAPTATION D'UNE STRUCTURE DE CONTACT POUR LA MISE EN CONTACT ÉLECTRIQUE D'UNE PUCE À SEMI-CONDUCTEUR OPTOÉLECTRONIQUE

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Application  
**EP 10763590 A 20100910**

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Abstract (en)  
[origin: WO2011038708A1] The invention relates to an optoelectronic semiconductor chip, comprising a first semiconductor functional area (21) having a first terminal (211) and a second terminal (212), and a contact structure (4) for electrically contacting the optoelectronic semiconductor chip, the contact structure being connected to the first semiconductor functional area (21) in an electrically conductive manner. The contact structure (4) has a conductor structure (41, 71, 42) that can be disconnected, wherein - when the conductor structure is not disconnected, an operating current path is established across the first terminal of the first semiconductor functional area and the second terminal, the operating current path being interrupted when the conductor structure is disconnected, or - when the conductor structure (41, 71, 42) is disconnected, an operating current path is established across the first terminal (211) of the first semiconductor functional area (21) and the second terminal (212), wherein when the conductor structure (41, 71, 42) is not disconnected, the conductor structure (41, 71, 42) connects the first terminal (211) to the second terminal (212) and short circuits the first semiconductor functional area (21).

IPC 8 full level  
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